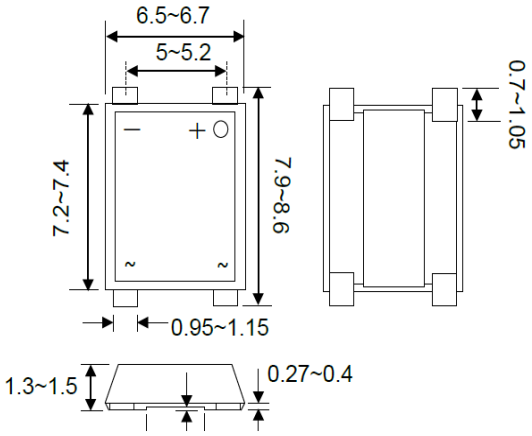
DBF2005 THRU DBF210

SINGLE-PHASE GLASS PASSIVATED SILICON SURFACE MOUNT BRIDGE RECTIFIER

Reverse Voltage - 50 to 1000 V
Forward Current - 2 A

DBF



All Dimensions in mm

Features

- Low forward voltage drop
- Glass passivated chip junction
- High surge current capability

Mechanical Data

- Case: Molded plastic, DBF
- Terminal: Leads solderable per MIL-STD-002, method 208 guaranteed
- Mounting position: Any

Maximum Ratings and Electrical Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load.For capacitive load, derate current by 20%.

Parameter	Symbols	DBF2005	DBF201	DBF202	DBF204	DBF206	DBF208	DBF210	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at T_C = 110 °C	$I_{F(AV)}$	2							A
Peak Forward Surge Current 8.3 ms Single Half-sine -wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	75							A
Maximum Forward Voltage at 2 A DC	V_F	1.1							V
Maximum Reverse Current at Rated DC Blocking Voltage T_j = 25°C T_j = 125°C	I_R	5 500							μA
Typical Junction Capacitance [1]	C_j	35							pF
Typical Thermal Resistance	$R_{\theta JA}$	55							°C/W
Typical Thermal Resistance	$R_{\theta JL}$	15							°C/W
Typical Thermal Resistance	$R_{\theta JC}$	10							°C/W
Operating and Storage Temperature Range	T_j , T_{stg}	- 55 to + 150							°C

[1] Measured at 1 MHz and applied reverse voltage of 4 Vdc.

FIG1:Io-Tc Curve

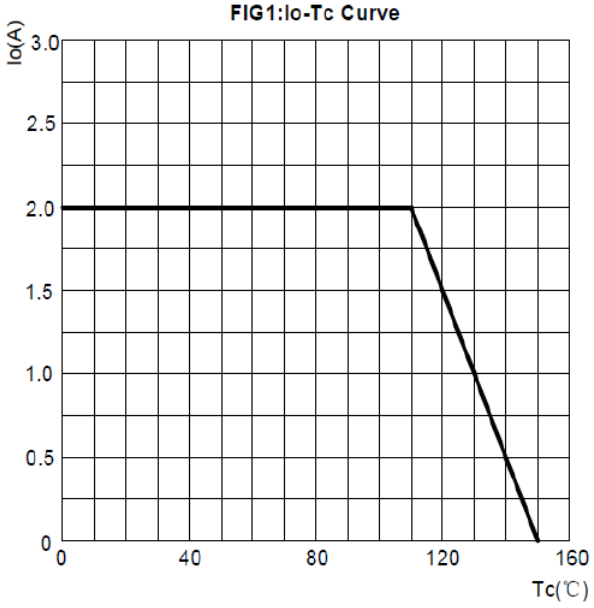


FIG2:Surge Forward Current Capadility

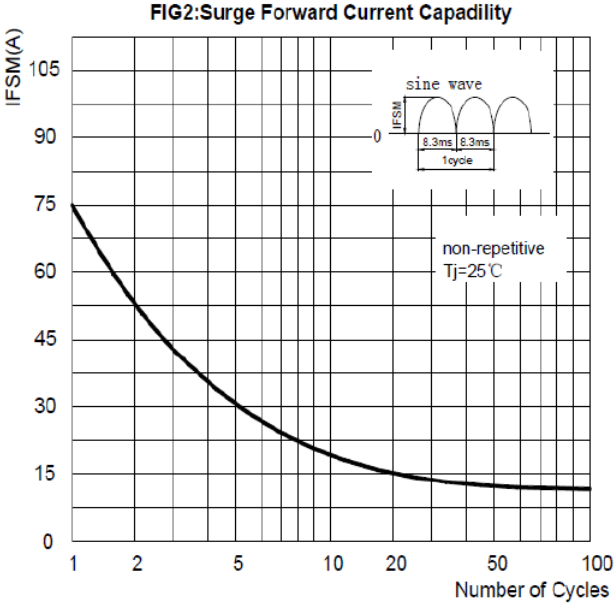


FIG3: Forward Voltage

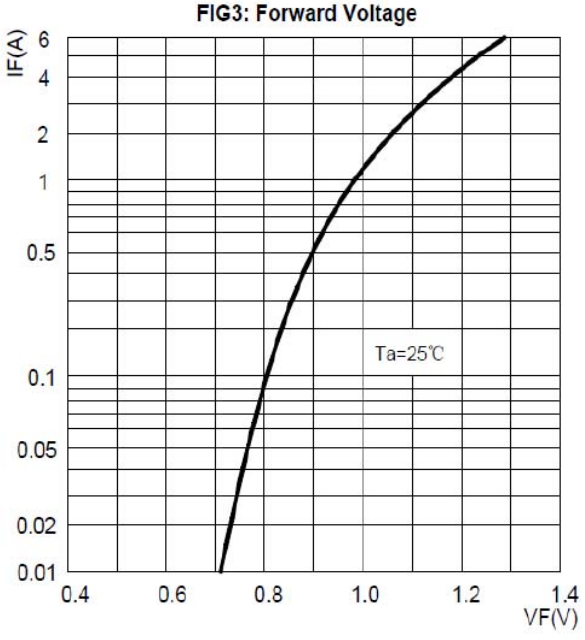


FIG4:Typical Reverse Characteristics